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Environment-dependent metastability of passivation-free indium zinc oxide thin film transistor after gate bias stress

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#	Paper	IF	Citations
191	High mobility and low operating voltage ZnGaO and ZnGaLiO transistors with spin-coated Al ₂ O ₃ as gate dielectric. <i>Journal Physics D: Applied Physics</i> , 2010 , 43, 442001	3	14
190	69.3: Amorphous Oxide TFT Backplane for Large Size AMOLED TVs. <i>Digest of Technical Papers SID International Symposium</i> , 2010 , 41, 1037	0.5	54
189	High stability of amorphous hafnium-indium-zinc-oxide thin film transistor. <i>Applied Physics Letters</i> , 2010 , 96, 152102	3.4	116
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182	Ambient Stability Enhancement of Thin-Film Transistor With InGaZnO Capped With InGaZnO:N Bilayer Stack Channel Layers. <i>IEEE Electron Device Letters</i> , 2011 , 32, 1397-1399	4.4	40
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11	High-Performance n-Channel Printed Transistors on Biodegradable Substrate for Transient Electronics. <i>Advanced Electronic Materials</i> , 2200098	6.4	4
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